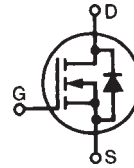


PolarHV™ HiPerFET Power MOSFET

IXFH 26N50P
IXFV 26N50P
IXFV 26N50PS

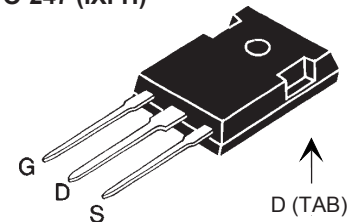
$V_{DSS} = 500 \text{ V}$
 $I_{D25} = 26 \text{ A}$
 $R_{DS(on)} \leq 230 \text{ m}\Omega$
 $t_{rr} \leq 200 \text{ ns}$

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

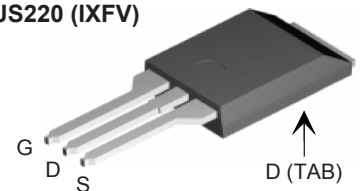


| Symbol | Test Conditions | Maximum Ratings | |
|------------|---|-----------------|------------------|
| | | | |
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 500 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$ | 500 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 26 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, pulse width limited by T_{JM} | 78 | A |
| I_{AR} | $T_C = 25^\circ\text{C}$ | 26 | A |
| E_{AR} | $T_C = 25^\circ\text{C}$ | 40 | mJ |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 1.0 | J |
| dv/dt | $I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 4 \Omega$ | 10 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 400 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| T_L | 1.6 mm (0.062 in.) from case for 10 s | 300 | $^\circ\text{C}$ |
| T_{SOLD} | Plastic body for 10 s | 260 | $^\circ\text{C}$ |
| M_d | Mounting torque (TO-247) | 1.13/10 | Nm/lb.in. |
| F_C | Mounting force (PLUS220) | 11..65/2.5..15 | N/lb |
| Weight | TO-247 | 6 | g |
| | PLUS220 & PLUS220SMD | 5 | g |

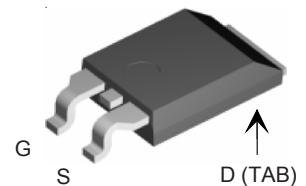
TO-247 (IXFH)



PLUS220 (IXFV)



PLUS220SMD (IXFV_S)



G = Gate D = Drain
S = Source TAB = Drain

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|--------------|--|-----------------------|------|----------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$ | 500 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$ | 3.0 | | 5.5 V |
| I_{GSS} | $V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$ | | | $\pm 100 \text{ nA}$ |
| I_{DSS} | $V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$ | | | 25 μA |
| | | | | 250 μA |
| $R_{DS(on)}$ | $V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$ | | | 230 $\text{m}\Omega$ |

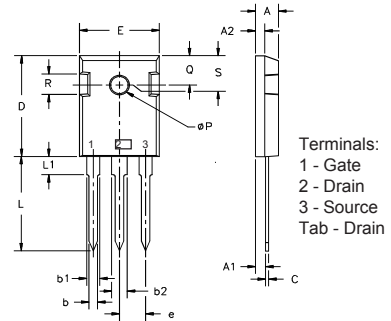
Features

- † International standard packages
- † Fast intrinsic diode
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
 - easy to drive and to protect

Advantages

- † Easy to mount
- † Space savings
- † High power density

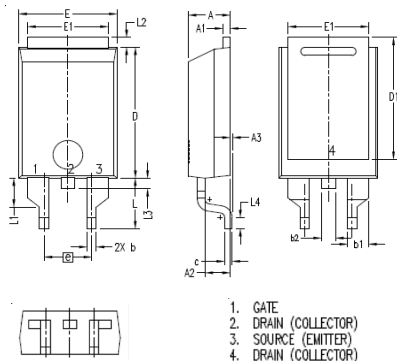
| Symbol | Test Conditions | Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|---|---|------|--------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 20\text{ V}$; $I_D = 0.5 I_{D25}$, pulse test | 16 | 26 | S |
| C_{iss} | $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$ | | 3600 | pF |
| C_{oss} | | | 370 | pF |
| C_{rss} | | | 40 | pF |
| $t_{d(on)}$ | $V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 I_{D25}$ $R_G = 4\ \Omega$ (External) | | 20 | ns |
| t_r | | | 25 | ns |
| $t_{d(off)}$ | | | 58 | ns |
| t_f | | | 20 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 0.5 I_{D25}$ | | 60 | nC |
| Q_{gs} | | | 20 | nC |
| Q_{gd} | | | 25 | nC |
| R_{thJC} | (TO-247, PLUS220) | | | $0.31\ ^\circ\text{C/W}$ |
| R_{thCS} | | | 0.21 | $^\circ\text{C/W}$ |

TO-247 AD (IXFH) Outline


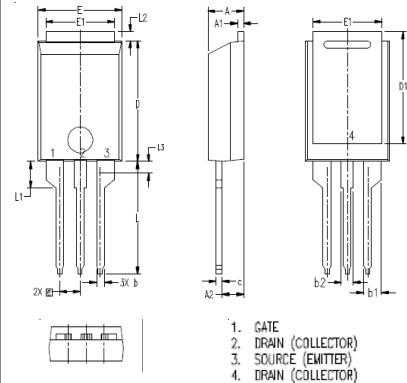
| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A ₁ | 2.2 | 2.54 | .087 | .102 |
| A ₂ | 2.2 | 2.6 | .059 | .098 |
| b | 1.0 | 1.4 | .040 | .055 |
| b ₁ | 1.65 | 2.13 | .065 | .084 |
| b ₂ | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L ₁ | | 4.50 | | .177 |
| ∅P | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |
| S | 6.15 | BSC | .242 | BSC |

Source-Drain Diode

| Symbol | Test Conditions | Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified) | | |
|----------|---|---|------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{ V}$ | | | 26 A |
| I_{SM} | Repetitive | | | 104 A |
| V_{SD} | $I_F = I_S$, $V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$ | | | 1.5 V |
| t_{rr} | $I_F = 25\text{ A}$, $-di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$, $V_{GS} = 0\text{ V}$ | | | 200 ns |
| Q_{RM} | | | 0.6 | μC |
| I_{RM} | | | 6 | A |

PLUS220SMD (IXFV_S) Outline


| SYM | INCHES | | MILLIMETER | |
|----------------|--------|------|------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .169 | .185 | 4.30 | 4.70 |
| A ₁ | .028 | .035 | 0.70 | 0.90 |
| A ₂ | .098 | .118 | 2.50 | 3.00 |
| A ₃ | .000 | .010 | 0.00 | 0.25 |
| b | .035 | .047 | 0.90 | 1.20 |
| b ₁ | .080 | .095 | 2.03 | 2.41 |
| b ₂ | .054 | .064 | 1.37 | 1.63 |
| c | .028 | .035 | 0.70 | 0.90 |
| D | .551 | .591 | 14.00 | 15.00 |
| D ₁ | .512 | .539 | 13.00 | 13.70 |
| E | .394 | .433 | 10.00 | 11.00 |
| E ₁ | .331 | .346 | 8.40 | 8.80 |
| e | .200 | BSC | 5.08 | BSC |
| L | .209 | .228 | 5.30 | 5.80 |
| L ₁ | .118 | .138 | 3.00 | 3.50 |
| L ₂ | .035 | .051 | 0.90 | 1.30 |
| L ₃ | .047 | .059 | 1.20 | 1.50 |
| L ₄ | .039 | .059 | 1.00 | 1.50 |

PLUS220 (IXFV) Outline


| SYM | INCHES | | MILLIMETER | |
|----------------|--------|------|------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .169 | .185 | 4.30 | 4.70 |
| A ₁ | .028 | .035 | 0.70 | 0.90 |
| A ₂ | .098 | .118 | 2.50 | 3.00 |
| b | .035 | .047 | 0.90 | 1.20 |
| b ₁ | .080 | .095 | 2.03 | 2.41 |
| b ₂ | .054 | .064 | 1.37 | 1.63 |
| c | .028 | .035 | 0.70 | 0.90 |
| D | .551 | .591 | 14.00 | 15.00 |
| D ₁ | .512 | .539 | 13.00 | 13.70 |
| E | .394 | .433 | 10.00 | 11.00 |
| E ₁ | .331 | .346 | 8.40 | 8.80 |
| e | .100 | BSC | 2.54 | BSC |
| L | .512 | .551 | 13.00 | 14.00 |
| L ₁ | .118 | .138 | 3.00 | 3.50 |
| L ₂ | .035 | .051 | 0.90 | 1.30 |
| L ₃ | .047 | .059 | 1.20 | 1.50 |

IXYS reserves the right to change limits, test conditions, and dimensions.

| | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|-------------|--------------|
| IXYS MOSFETs and IGBTs are covered by | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 |
| one or more of the following U.S. patents: | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405B2 | 6,759,692 |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 |

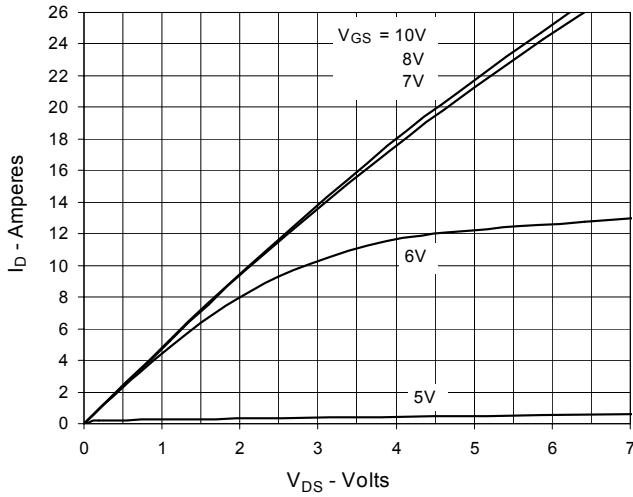
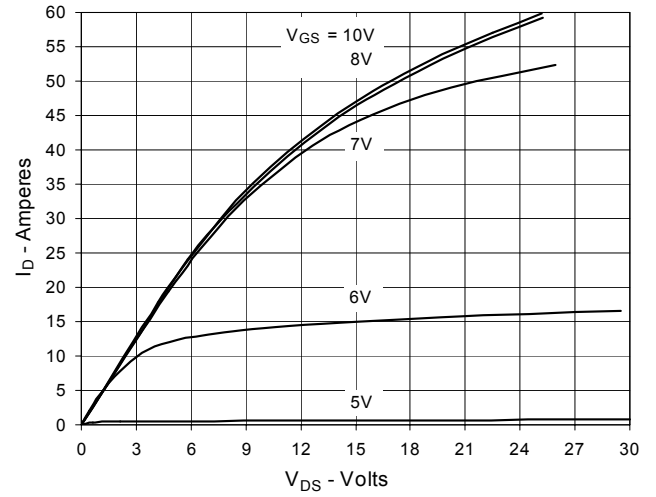
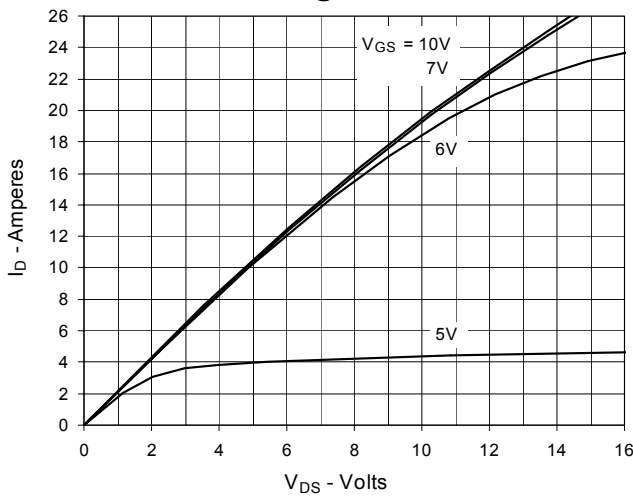
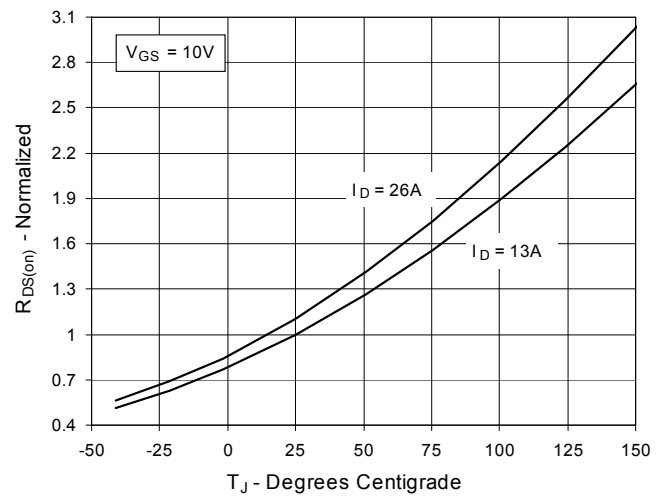
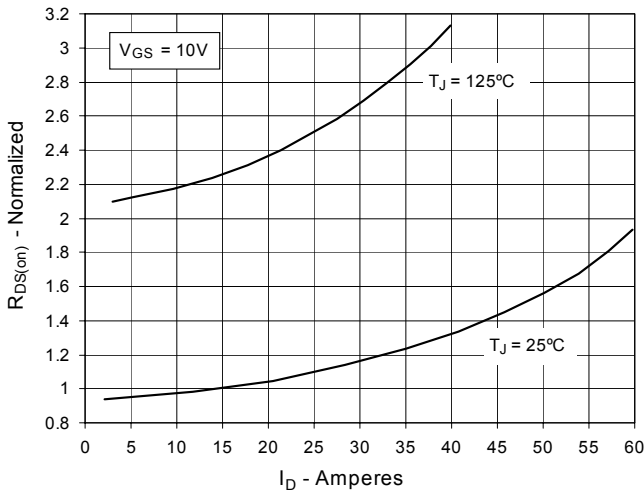
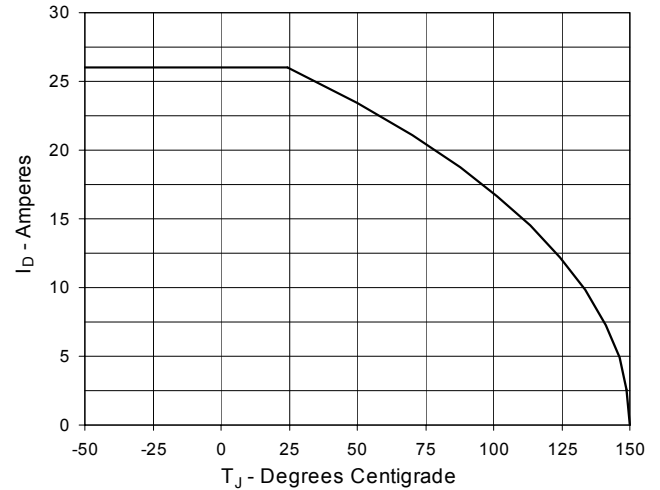
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 125°C**

**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 13A$ Value
vs. Junction Temperature**

**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 13A$ Value
vs. Drain Current**

**Fig. 6. Maximum Drain Current vs.
Case Temperature**


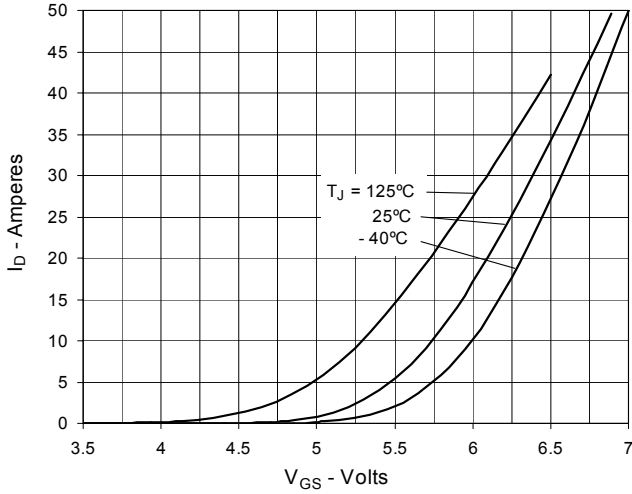
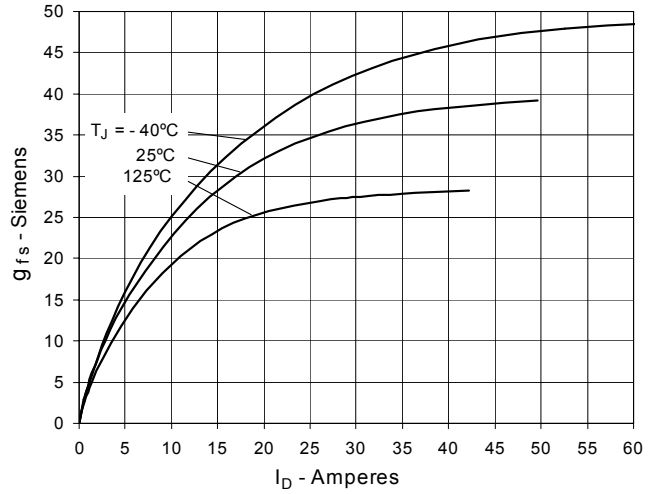
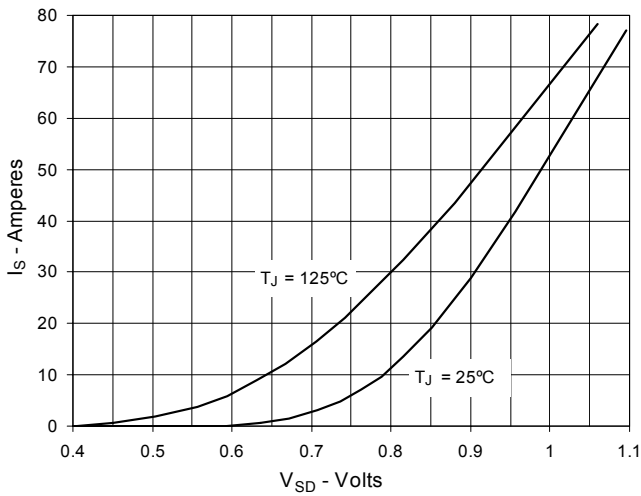
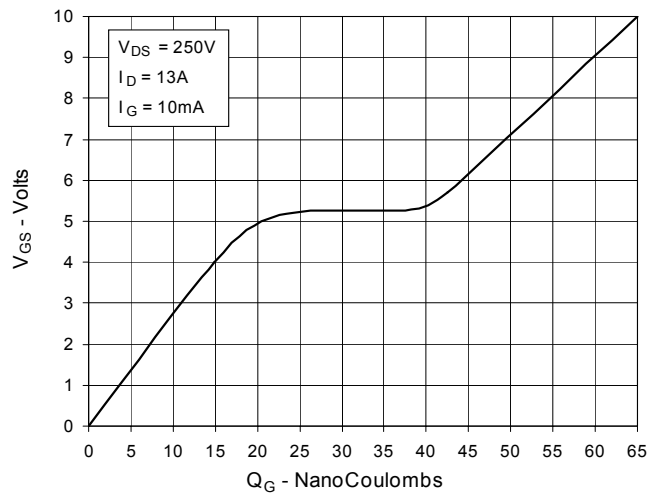
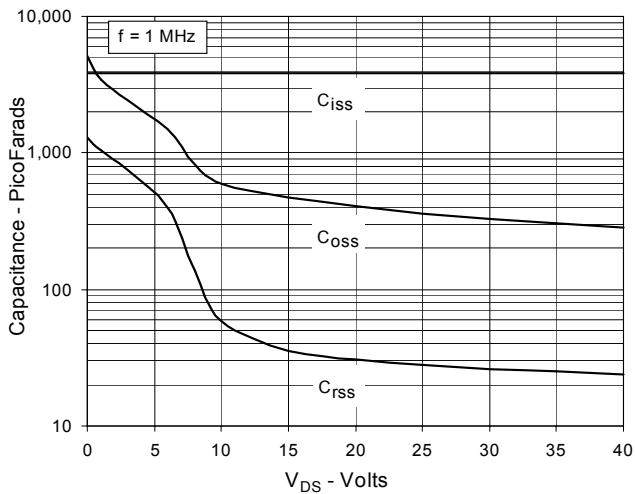
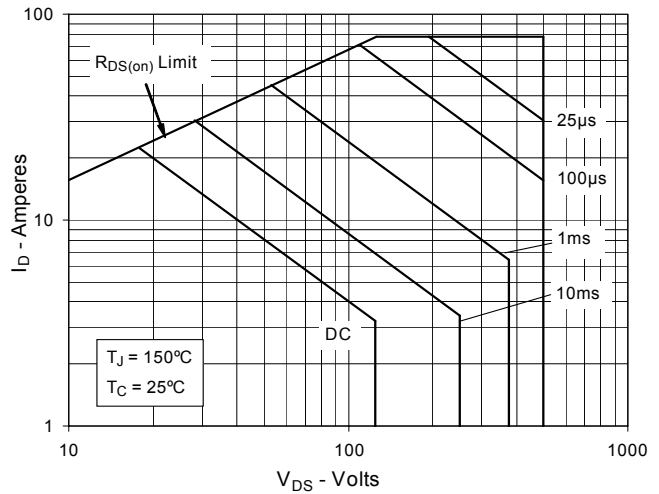
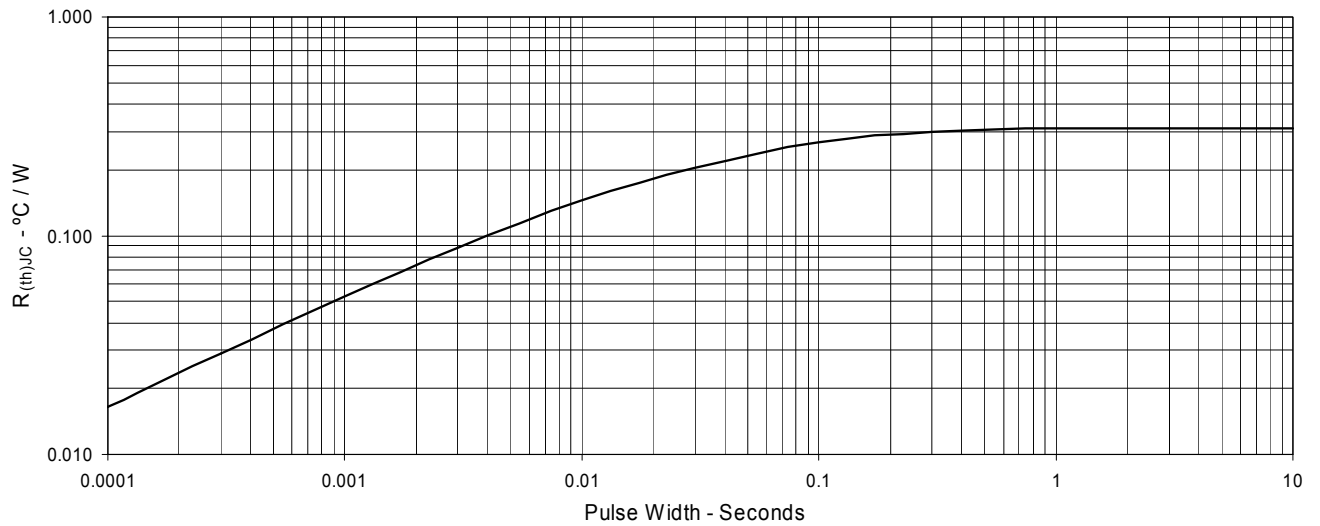
Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Forward-Bias Safe Operating Area


Fig. 13. Maximum Transient Thermal Resistance





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